

**FAIRCHILD**  
SEMICONDUCTOR®

**QFET®**

## FQP32N20C/FQPF32N20C

### 200V N-Channel MOSFET

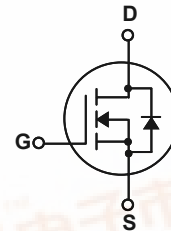
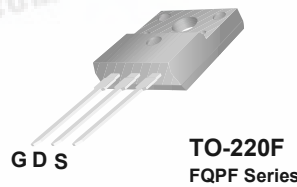
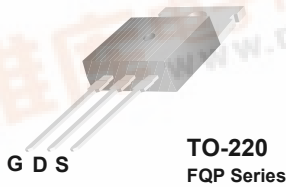
#### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supplies and motor controls.

#### Features

- 28A, 200V,  $R_{DS(on)} = 0.082\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 82.5 nC)
- Low Crss ( typical 185 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FQP32N20C	FQPF32N20C	Units
V <sub>DSS</sub>	Drain-Source Voltage	200		V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	28.0	28.0 *	A
		17.8	17.8 *	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	112	112 *	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30		V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	955		mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	28.0		A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	15.6		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5		V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	156	50	W
		1.25	0.4	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150		°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

\* Drain current limited by maximum junction temperature.

#### Thermal Characteristics

Symbol	Parameter	FQP32N20C	FQPF32N20C	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	0.8	2.51	°C/W
R <sub>θJS</sub>	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W



## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	200	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.24	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 14\text{ A}$	--	0.068	0.082	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 14\text{ A}$ (Note 4)	--	20	--	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1700	2220	pF
$C_{oss}$	Output Capacitance		--	400	520	pF
$C_{rss}$	Reverse Transfer Capacitance		--	185	245	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 32\text{ A},$ $R_G = 25\ \Omega$  (Note 4, 5)	--	25	60	ns
$t_r$	Turn-On Rise Time		--	270	550	ns
$t_{d(off)}$	Turn-Off Delay Time		--	245	500	ns
$t_f$	Turn-Off Fall Time		--	210	430	ns
$Q_g$	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 32\text{ A},$ $V_{GS} = 10\text{ V}$  (Note 4, 5)	--	82.5	110	nC
$Q_{gs}$	Gate-Source Charge		--	10.5	--	nC
$Q_{gd}$	Gate-Drain Charge		--	44.5	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	28	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	112	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 28\text{ A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 32\text{ A},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	265	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	2.73	--	$\mu\text{C}$

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 1.4\text{ mH}, I_{AS} = 32\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 28\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

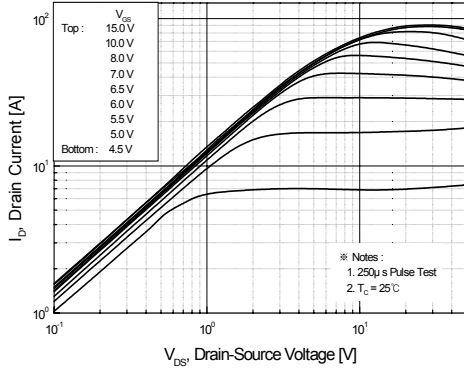


Figure 1. On-Region Characteristics

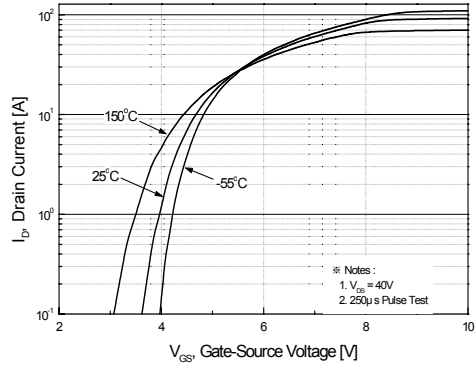


Figure 2. Transfer Characteristics

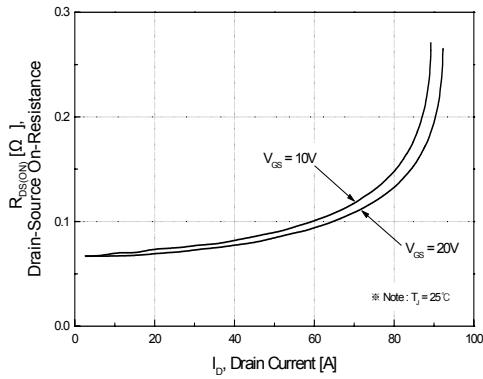


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

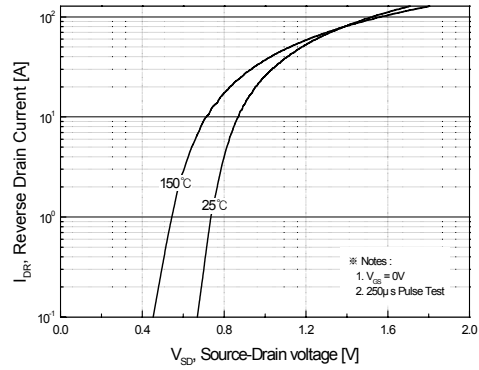


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

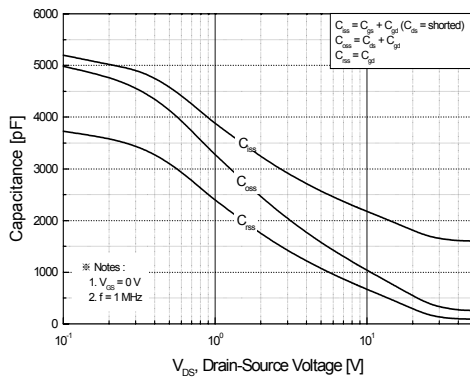


Figure 5. Capacitance Characteristics

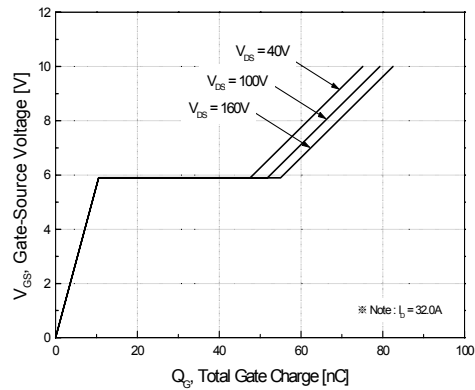
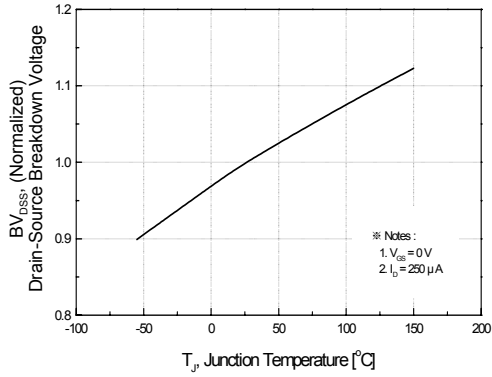
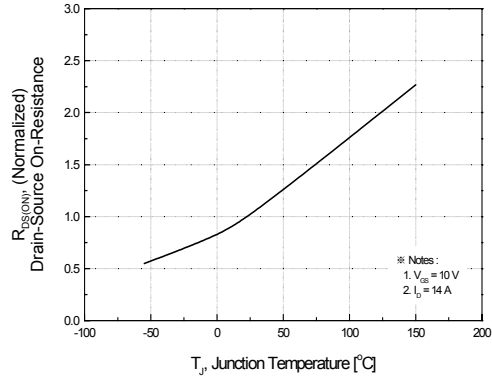


Figure 6. Gate Charge Characteristics

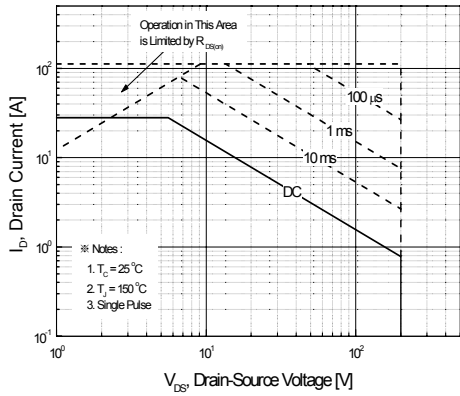
**Typical Characteristics** (Continued)



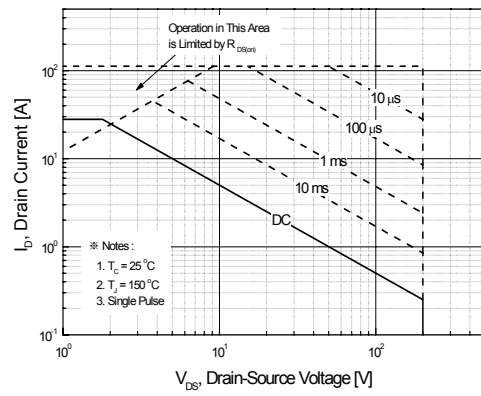
**Figure 7. Breakdown Voltage Variation vs Temperature**



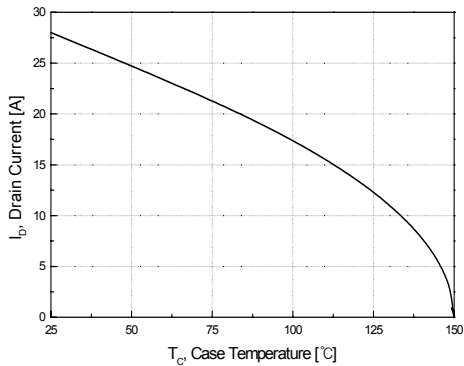
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9-1. Maximum Safe Operating Area for FQP32N20C**

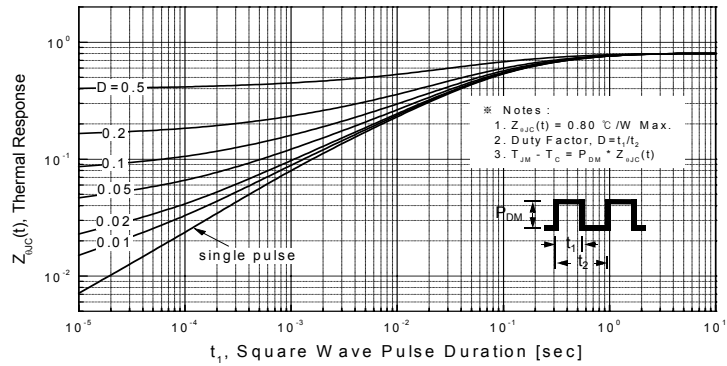


**Figure 9-2. Maximum Safe Operating Area for FQPF32N20C**

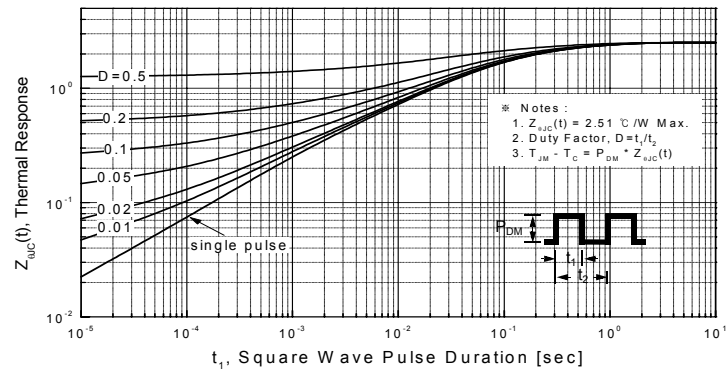


**Figure 10. Maximum Drain Current vs Case Temperature**

**Typical Characteristics** (Continued)

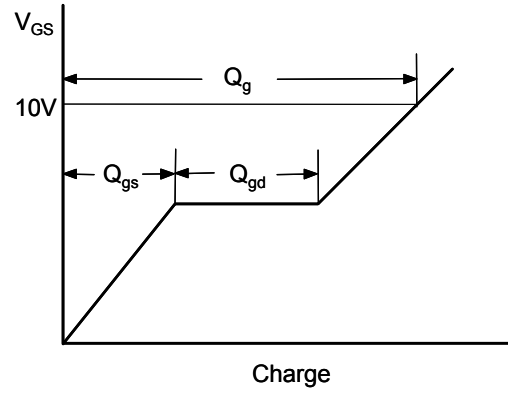
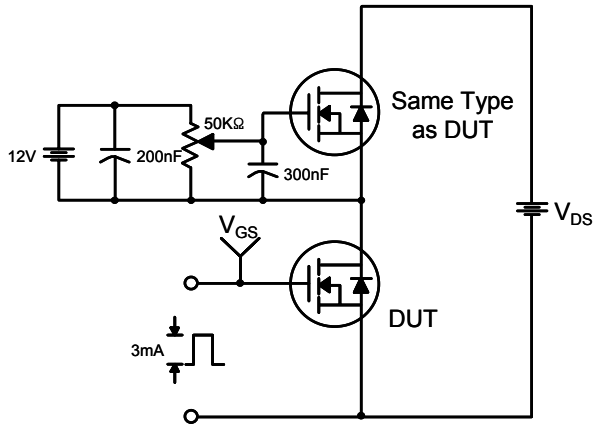


**Figure 11-1. Transient Thermal Response Curve for FQP32N20C**

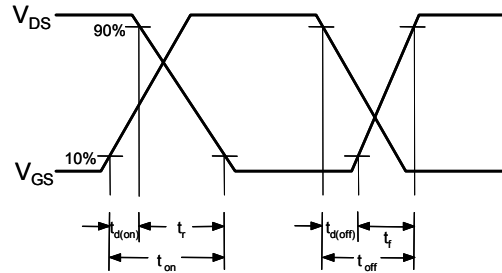
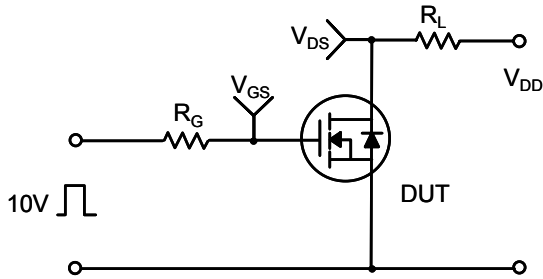


**Figure 11-2. Transient Thermal Response Curve for FQPF32N20C**

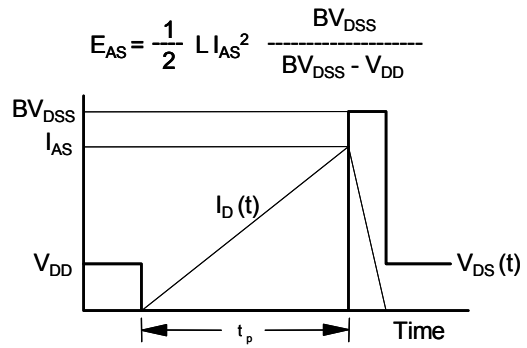
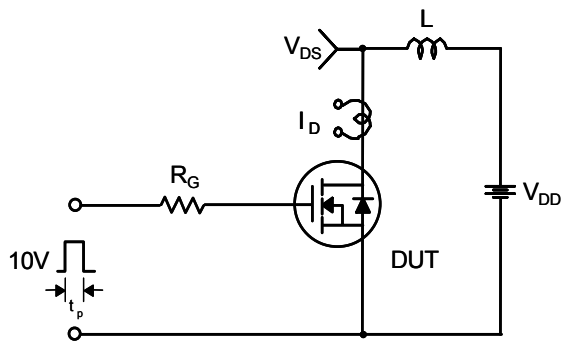
**Gate Charge Test Circuit & Waveform**



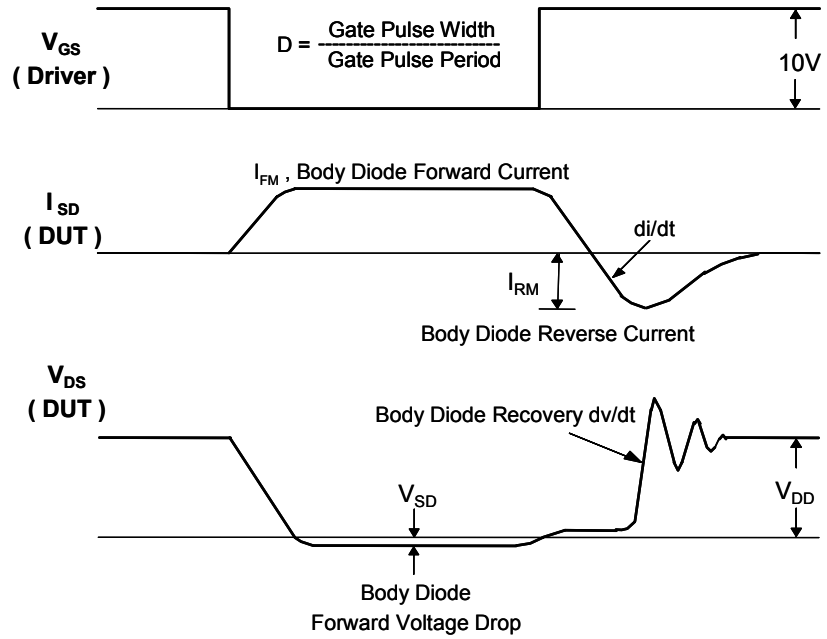
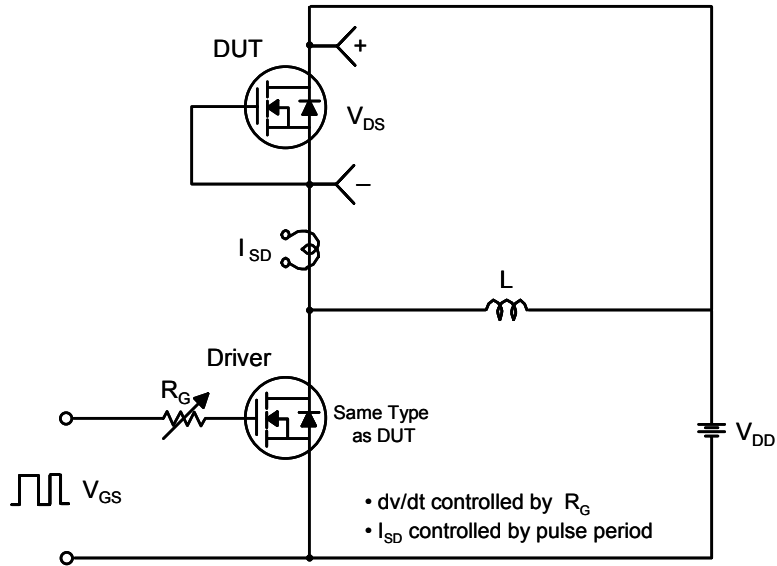
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

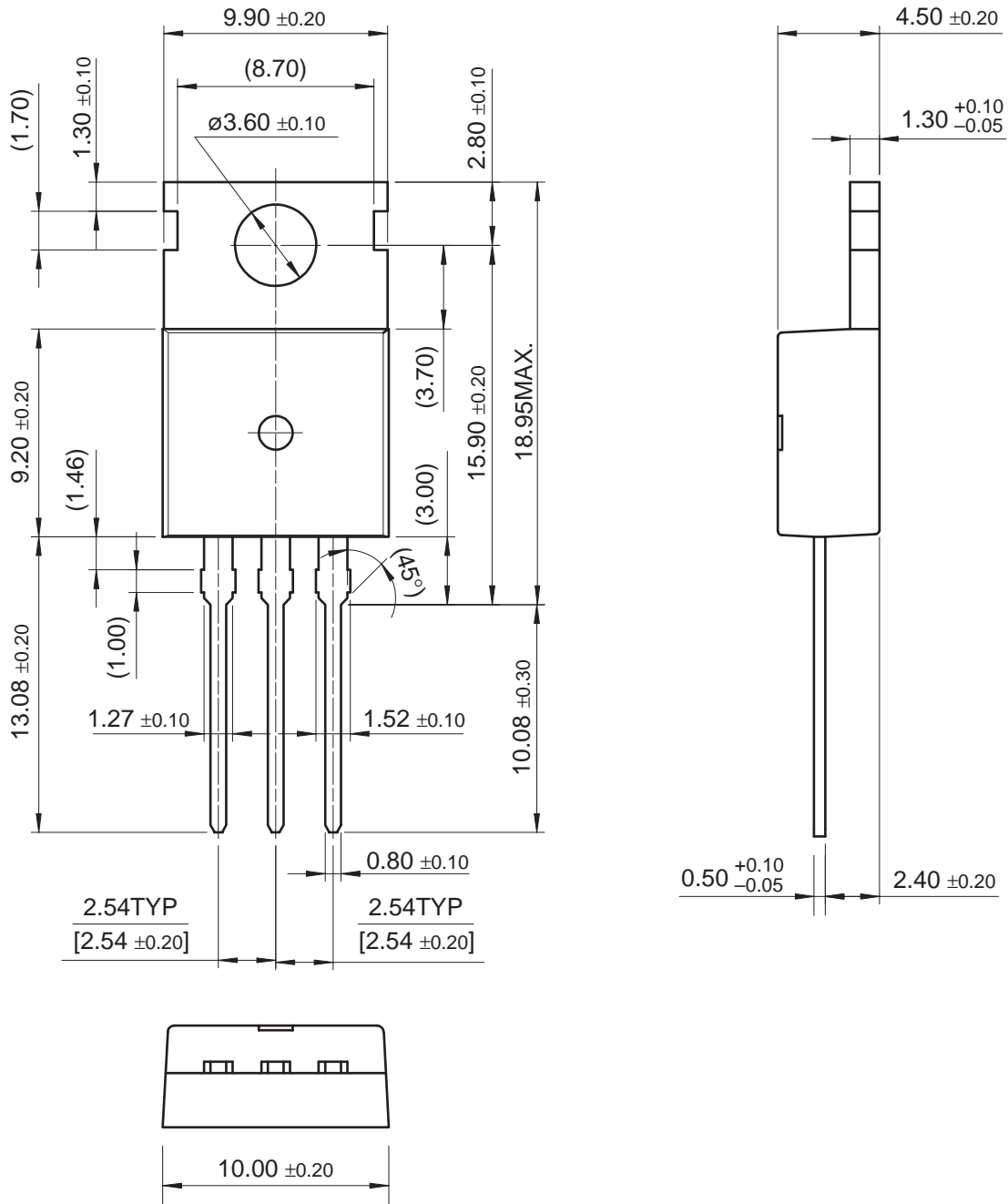


Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Package Dimensions

## TO-220



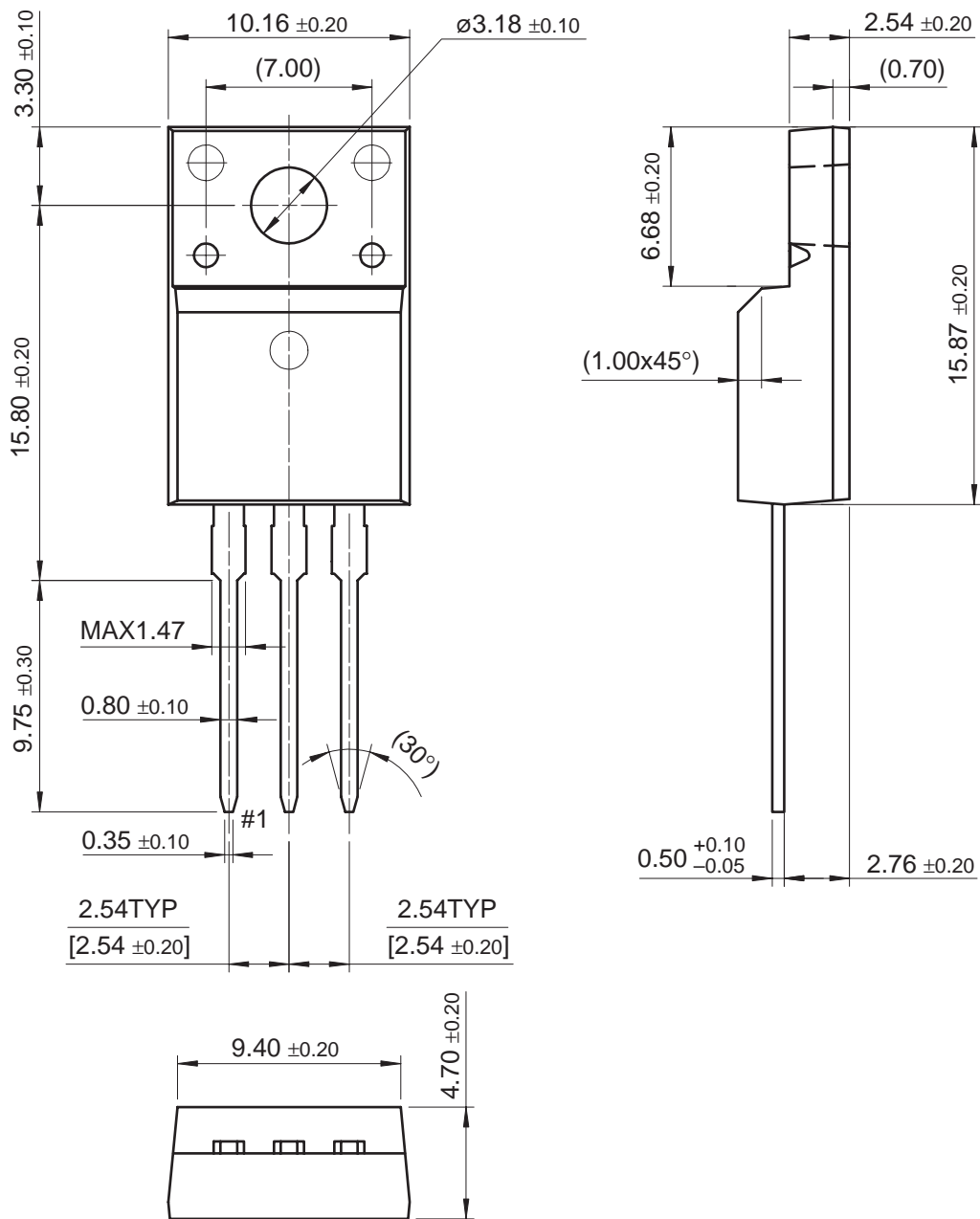
FQP32N20C/FQPF32N20C

Dimensions in Millimeters



Package Dimensions (Continued)

TO-220F



FQP32N20C/FQPF32N20C

Dimensions in Millimeters

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DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
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